

Docket No. \_\_\_\_\_

## **DECLARATION AND POWER OF ATTORNEY**

As a below named inventor(s), I/we hereby declare that:

My/Our residence(s), post office address(es) and citizenship(s) are as stated below next to my/our name(s);

I/We believe that I/we am/are the original, first and sole/joint inventor(s) of the subject matter claimed and for which patent is sought on the invention entitled:

OPTICAL PATH DEVICE

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the specification of which:

[ X ] is attached hereto [ ] was filed on \_\_\_\_\_ as Application Serial No. \_\_\_\_\_  
and was amended on \_\_\_\_\_ (if applicable).

I/We hereby state that I/we have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I/We acknowledge the duty to disclose information which is known to me/us to be material to patentability in accordance with Title 37, Code of Federal Regulations, Section 1.56.

I/We hereby claim foreign priority benefits under Title 35, United States Code, Section 119 (a)-(d) or section 365(b) of any foreign application(s) for patent or inventors' certificate, or Section 365(a) of any PCT international application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

<b>Prior Foreign Application(s):</b>			<b><u>Priority Claimed</u></b>	
<b><u>Number</u></b>	<b><u>Country</u></b>	<b><u>Day/Month/Year Filed</u></b>	<b><u>Yes</u></b>	<b><u>No</u></b>
91216964	TAIWAN, R.O.C.	October 23, 2002	X	

I/We hereby claim the benefit under 35 USC § 119(e) of any United States provisional application(s) listed below.

**Prior Provisional Application(s):**  
**Application Number**                      **Filing Date**

I/We hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s) listed below, and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, Section 112, I/we acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, Section 1.56(a) which occurred between the filing date

of the prior date of the prior application and the national or PCT international filing date of this application:

**Prior U.S. Application(s)**

**Serial No.**

**Filing Date**

**Status: Patented, Pending, Abandoned**

I/We hereby declare that all statements made herein of my/our own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

I/We hereby appoint the following attorney(s) and/or agent(s): Allan M. Lowe, Reg. No. 19,641; Israel Gopstein, Reg. No. 27,333; Benjamin J. Hauptman, Reg. No. 29,310; Kenneth M. Berner, Reg. No. 37,093; Michael G. Gilman, Reg. No. 19,114; Albert J. Fasulo, Reg. No. 43,607; and Randy Noranbrock, Reg. No. 42,940; all of

LOWE HAUPTMAN GOPSTEIN GILMAN & BERNER, LLP  
1700 Diagonal Road, Suite 310  
Alexandria, Virginia 22314

with full power of substitution and revocation, to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith, and all further correspondence should be addressed to them.

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Full name of sole or first Inventor: Chin-Chung LIEN

Inventor's signature:

*Chin-Chung Lien*

Date:

July 17, 2003

Residence:

2E, NO.2, ALLEY 1, LANE 109, HSIU FENG RD., HSI CHIH CITY, TAIPEI, TAIWAN, R.O.C.

Citizenship:

TAIWAN, R.O.C.

Post Office Address:

NO.1-1, R&D RD.2, SCIENCE-BASED INDUSTRIAL PARK, HSINCHU, TAIWAN, R.O.C.

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